	Application No.	Applicant(s)
Notice of Allowability	10/767,276 Examiner	ANG ET AL. Art Unit
	Thanhha Pham	2813
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	is (OR REMAINS) CLOSED in or other appropriate communication is selection in second communication in s	n this application. If not included unication will be mailed in due course. THIS
1. This communication is responsive to <u>08/02/2005</u> .		
2. The allowed claim(s) is/are 1.3-27 and 42.		
3. ☐ Acknowledgment is made of a claim for foreign priority unallocation a) ☐ All b) ☐ Some* c) ☐ None of the:	nder 35 U.S.C. § 119(a)-(d)	or (f).
 Certified copies of the priority documents have 	e been received.	
Certified copies of the priority documents have	e been received in Application	on No
Copies of the certified copies of the priority do	ocuments have been received	d in this national stage application from the
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the requirements
4. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which giv		
5. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.	
(a) ☐ including changes required by the Notice of Draftspers		v (PTO-948) attached
1) hereto or 2) to Paper No./Mail Date		
(b) including changes required by the attached Examiner	's Amendment / Comment or	in the Office action of
Paper No./Mail Date		
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t		
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT 		
Attachment(s)	5 🗆 Nation of In	formal Detail Application (DTO 152)
1. Notice of References Cited (PTO-892)		formal Patent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)		ummary (PTO-413), Mail Date
3. Information Disclosure Statements (PTO-1449 or PTO/SB/0		Amendment/Comment
Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. 🛭 Examiner's	Statement of Reasons for Allowance
- Diological Matorial	9. 🗌 Other	<u>-</u> -

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EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mark Marcelli on 09/30/2005.

The application has been amended as follows:

- In claim 1,
 - line 5, after "planar" insert top -
- In claim 4,

line 4, change "stop" to - stopping -

• In claim 12,

line 4, change "said polishing stop layer" to - said polish stopping layer -

In claim 42,

line 3, after "planar" insert - top --

Allowable Subject Matter

- 2. Claims 1, 4-27 and 42 are allowed.
- 3. The following is an examiner's statement of reasons for allowance: Recorded Prior Art fails to disclose or suggest the combination of the process steps of method to polish down conductive lines in the manufacture of an integrated circuit device as

recited in the base claim 1 including: depositing a high density plasma (HDP) oxide layer overlying said substrate and said conductive lines wherein, in the regions between said conductive lines, first planar top surfaces of said HDP oxide layer are formed below the top of said conductive lines; and polishing down said film layer, said polish stopping layer, said HDP oxide layer and said conductive lines to portions of said polish stopping layer overlying said first top planar surfaces to complete said polishing down of said conductive lines. Recorded Prior Art also fails to disclose or suggest the combination of the process steps of method to polish down polysilicon lines in the manufacture of an integrated circuit device as recited in the base claim 11 including: depositing a high density plasma (HDP) oxide layer overlying said substrate and said polysilicon lines wherein, in the regions between said polysilicon lines, first planar top surfaces of said HDP oxide layer are formed below the top of said polysilicon lines; and polishing down said film layer, said polish stopping layer, said HDP oxide layer and said polysilicon lines to said polish stopping layer overlying said first top planar surfaces to complete said polishing down of said polysilicon lines. Recorded Prior Art also fails to disclose or suggest the combination of the process steps of method to form anti-fuse memory devices in the manufacture of an integrated circuit device as recited in the base claim 19 including: depositing a high density plasma (HDP) oxide layer overlying said substrate and said n-type polysilicon lines wherein, in the regions between said n-type polysilicon lines, first planar top surfaces of said HDP oxide layer are formed below the top of said n-type polysilicon lines; and polishing down said film layer, said polish stopping layer, said HDP oxide layer and said n-type polysilicon lines to said polish

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stopping layer overlying said first top planar surfaces to complete said polishing down of said n-type polysilicon lines.

4. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanhha Pham whose telephone number is (571) 272-1696. The examiner can normally be reached on Monday and Thursday 9:00AM - 9:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead can be reached on (571) 272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Thanhha Pham

LAURA M. SCHILLINGER

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